

IN THE CLAIMS:

Please amend the claims as follows:

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fig. 1
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1. (Amended) A [semiconductor device] ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said [semiconductor device] CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT [has] having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

wherein said first impurity region of said n-channel TFT is disposed so as to [completely] partially [overlap[s]] with [said second conductive layer] a portion of said second conductive layer which is in contact with said gate insulating film;

wherein said third impurity region of said p-channel TFT is disposed so as to partially [overlap[s]] with [said second conductive layer] another portion of said second conductive layer which is in contact with said gate insulating film.

Please add following claims.

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2. A ferroelectric liquid crystal display device according to claim 1, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).-4

#-3. A ferroelectric liquid crystal display device according to claim 1, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers.-4

#-4. A ferroelectric liquid crystal display device according to claim 1, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).-4

Sub C2
#-5. A ferroelectric liquid crystal display device according to claim 1, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.-4

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#-6. A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

5 each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

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a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

10 wherein said first impurity region of said n-channel TFT is disposed so as to partially
12 [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

15 wherein said second impurity region of said n-channel TFT is disposed so as not to
[overlaps] with said second conductive ^{layer} [film];

17 wherein said third impurity region of said p-channel TFT is disposed so as to partially
[overlaps] with ^a [said] portion which said second conductive layer is in contact with said gate insulating film. 4

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7. A ferroelectric liquid crystal display device according to claim 6, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). 4

112 1st 8. A ferroelectric liquid crystal display device according to claim 6, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers. -5

9. A ferroelectric liquid crystal display device according to claim 6, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

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10. A ferroelectric liquid crystal display device according to claim 6, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

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11. A ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

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a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region;

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wherein said first impurity region is disposed so as to partially overlaps with said first gate electrode, and

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said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film, said second semiconductor layer comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

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wherein said third impurity region is disposed so as to partially overlaps with said second gate electrode.

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12. A ferroelectric liquid crystal display device according to claim 11, wherein said first and second gate^{electrodes} comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

13. A ferroelectric liquid crystal display device according to claim 11, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

p. 57, fig. 15D
14. A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

wherein said first impurity region of said n-channel TFT is disposed so as to partially [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

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wherein said third impurity region of said p-channel TFT is disposed so as to partially
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[overlaps] with [said] portion which said second conductive layer is in contact with said gate insulating
film. ¶

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15. A goggle type display device according to claim 14, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). ¶

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16. A goggle type display device according to claim 14, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers. ¶

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17. A goggle type display device according to claim 14, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). ¶

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18. A goggle type display device according to claim 14, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region. ¶

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19. A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

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each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

10 a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

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wherein said first impurity region of said n-channel TFT is disposed so as to partially [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

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wherein said second impurity region of said n-channel TFT is disposed so as not to [overlaps] with said second conductive ^{layer} [film];

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wherein said third impurity region of said p-channel TFT is disposed so as to partially [overlaps] with ^a [said] portion which said second conductive layer is in contact with said gate insulating film. 4

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20. A goggle type display device according to claim 19, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). 4

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21. A goggle type display device according to claim 19, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers.

22. A goggle type display device according to claim 19, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

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23. A goggle type display device according to claim 19, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

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24. A goggle type display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

5 a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region;

wherein said first impurity region is disposed so as to partially [overlaps] with said first gate electrode, and

10 said p-channel TFT comprising:

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15 a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film, said second semiconductor layer comprising a second channel formation region and a third impurity region being in contact with said second channel formation region, wherein said third impurity region is disposed so as to partially overlaps with said second gate electrode.

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25. A goggle type display device according to claim 24, wherein said first and second gate^{electrodes} [electrode] comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

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26. A goggle type display device according to claim 24, wherein [said first impurity region] is a LDD region, [said second impurity region] is a source or a drain region, and [said third impurity region] is the source or the drain region.

REMARKS

I. Title

In the Office Action, the Examiner objects to the title of the invention as not being descriptive. Accordingly, Applicants are amending the title to recite -- Ferroelectric Liquid Crystal and Goggle Type Display Devices -- , which is consistent with the claims herein. Therefore, it is requested that this rejection be withdrawn.